

IRFZ34NSPbF IRFZ34NLPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Surface Mount (IRFZ34NS)
- Low-profile through-hole (IRFZ34NL)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

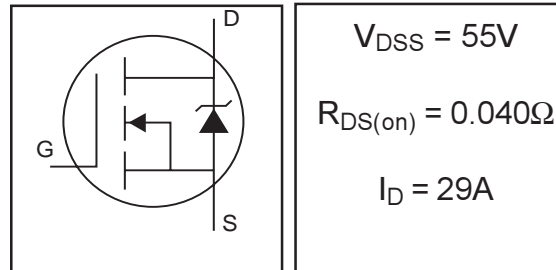
The through-hole version (IRFZ34NL) is available for low-profile applications.

Absolute Maximum Ratings

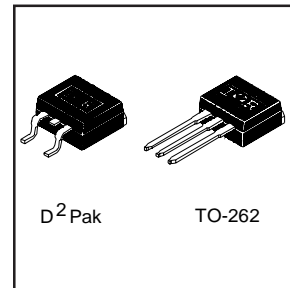
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ Ⓞ	29	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ Ⓞ	20	
I_{DM}	Pulsed Drain Current ① ⑤	100	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy② ⑤	130	mJ
I_{AR}	Avalanche Current④	16	A
E_{AR}	Repetitive Avalanche Energy④	5.6	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ⑤	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **	---	40	



$V_{DSS} = 55\text{V}$
$R_{DS(on)} = 0.040\Omega$
$I_D = 29\text{A}$



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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.052	—	V/°C	Reference to 25°C, I _D = 1mA [Ⓞ]
R _{DS(ON)}	Static Drain-to-Source On-Resistance	—	—	0.040	Ω	V _{GS} = 10V, I _D = 16A [Ⓞ]
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	6.5	—	—	S	V _{DS} = 25V, I _D = 16A
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 55V, V _{GS} = 0V
		—	—	250	μA	V _{DS} = 44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100	nA	V _{GS} = -20V
Q _g	Total Gate Charge	—	—	34	nC	I _D = 16A
Q _{gs}	Gate-to-Source Charge	—	—	6.8	nC	V _{DS} = 44V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	14	nC	V _{GS} = 10V, See Fig. 6 and 13 [Ⓞ] [Ⓟ]
t _{d(on)}	Turn-On Delay Time	—	7.0	—	ns	V _{DD} = 28V
t _r	Rise Time	—	49	—		I _D = 16A
t _{d(off)}	Turn-Off Delay Time	—	31	—		R _G = 18Ω
t _f	Fall Time	—	40	—		R _D = 1.8Ω, See Fig. 10 [Ⓞ] [Ⓟ]
L _S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C _{iss}	Input Capacitance	—	700	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	240	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	100	—		f = 1.0MHz, See Fig. 5 [Ⓟ]

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	29	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) [Ⓛ]	—	—	100		
V _{SD}	Diode Forward Voltage	—	—	1.6	V	T _J = 25°C, I _S = 16A, V _{GS} = 0V [Ⓞ]
t _{rr}	Reverse Recovery Time	—	57	86	ns	T _J = 25°C, I _F = 16A
Q _{rr}	Reverse Recovery Charge	—	130	200	nC	di/dt = 100A/μs [Ⓞ] [Ⓟ]
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

[Ⓛ] Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

[Ⓞ] V_{DD} = 25V, starting T_J = 25°C, L = 610μH
R_G = 25Ω, I_{AS} = 16A. (See Figure 12)

[Ⓟ] I_{SD} ≤ 16 A, di/dt ≤ 420A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C

[Ⓠ] Pulse width ≤ 300μs; duty cycle ≤ 2%.

[Ⓡ] Uses IRFZ34N data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

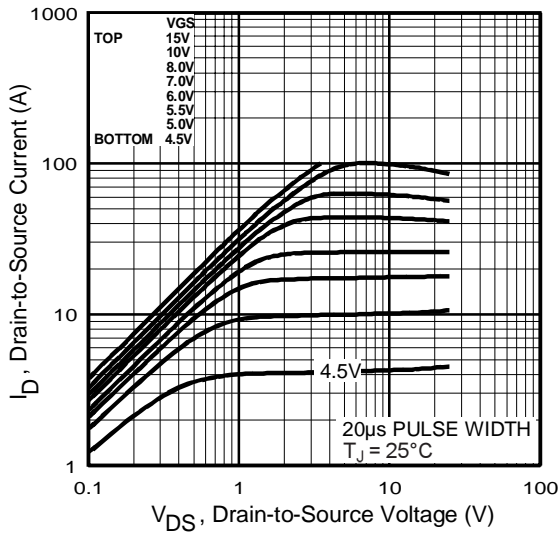


Fig 1. Typical Output Characteristics

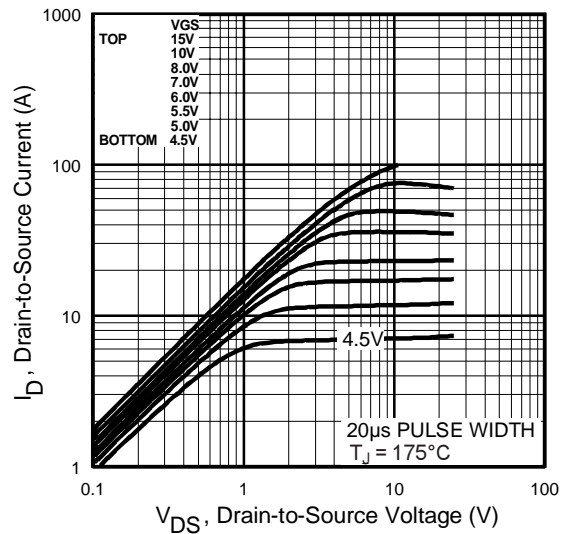


Fig 2. Typical Output Characteristics

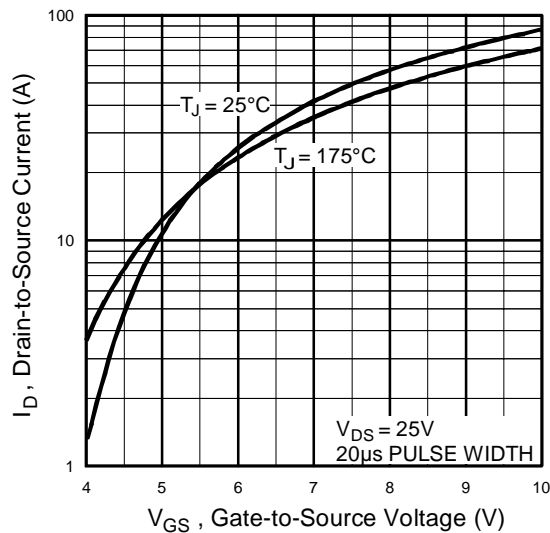


Fig 3. Typical Transfer Characteristics

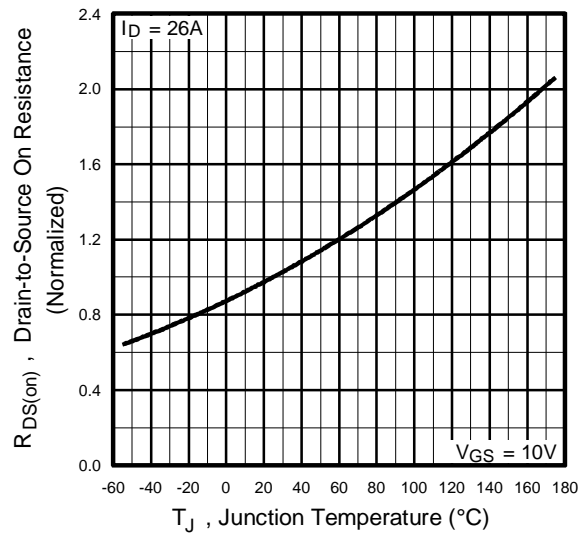


Fig 4. Normalized On-Resistance Vs. Temperature

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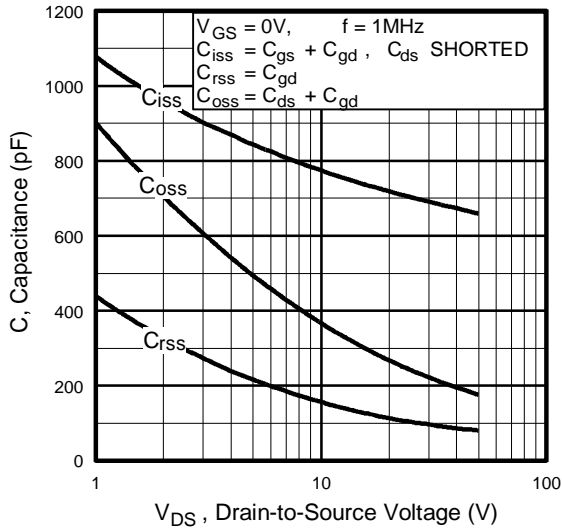


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

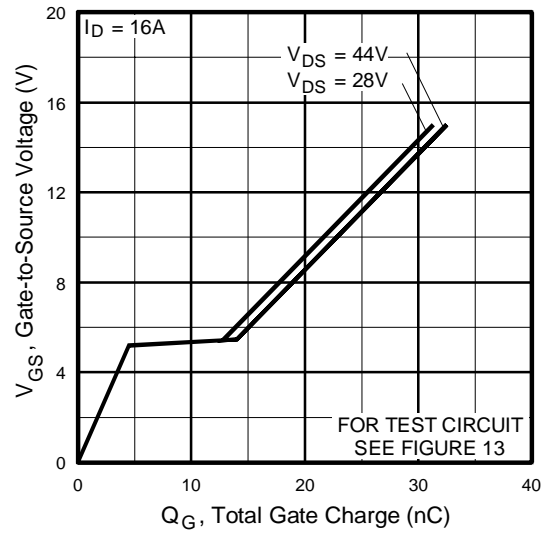


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

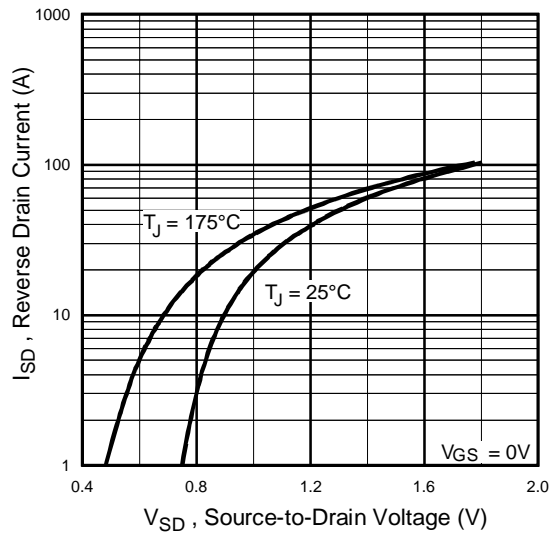


Fig 7. Typical Source-Drain Diode Forward Voltage

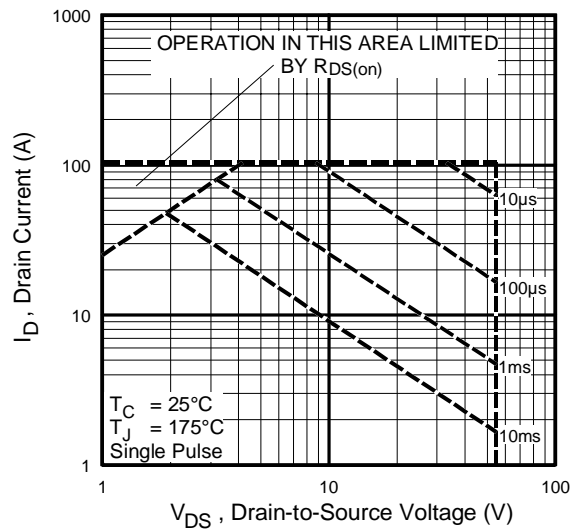


Fig 8. Maximum Safe Operating Area

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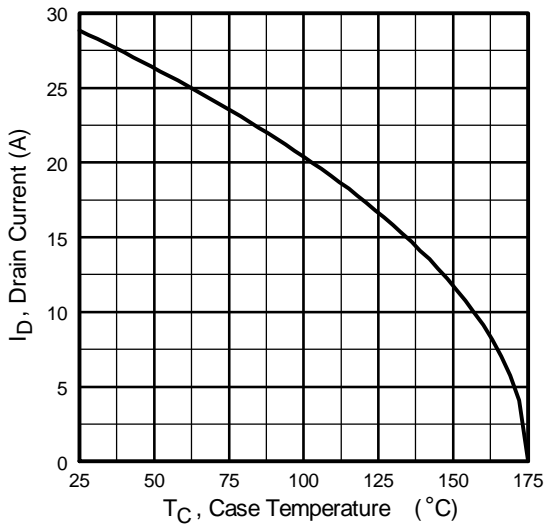


Fig 9. Maximum Drain Current Vs. Case Temperature

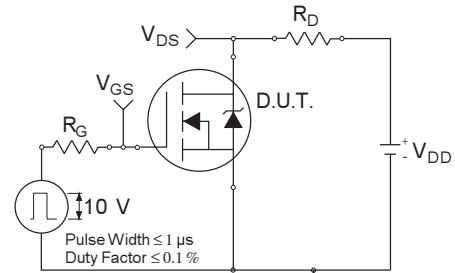


Fig 10a. Switching Time Test Circuit

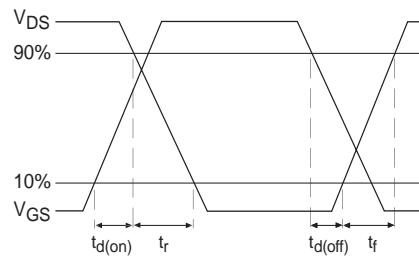


Fig 10b. Switching Time Waveforms

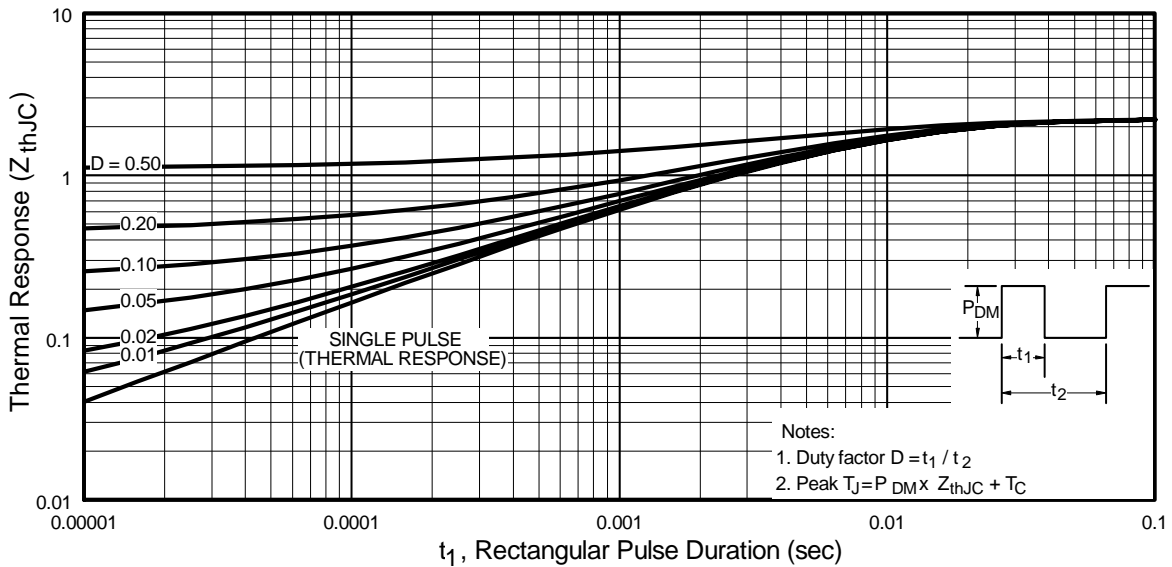


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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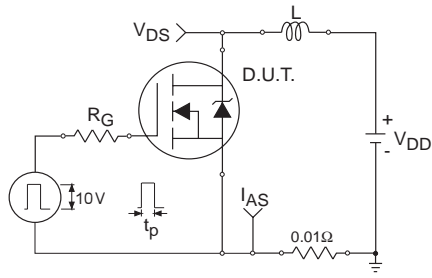


Fig 12a. Unclamped Inductive Test Circuit

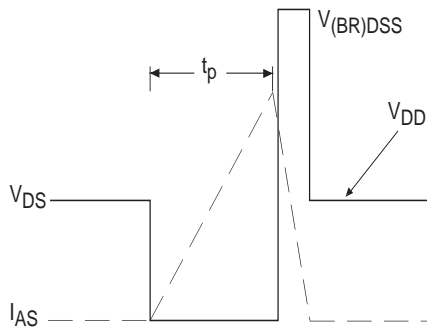


Fig 12b. Unclamped Inductive Waveforms

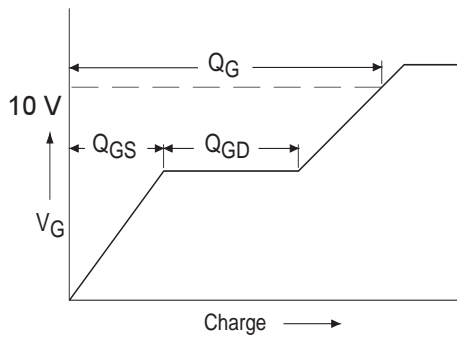


Fig 13a. Basic Gate Charge Waveform

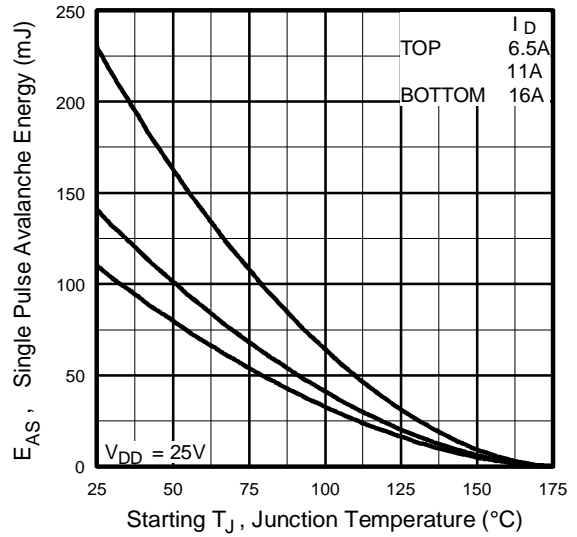


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

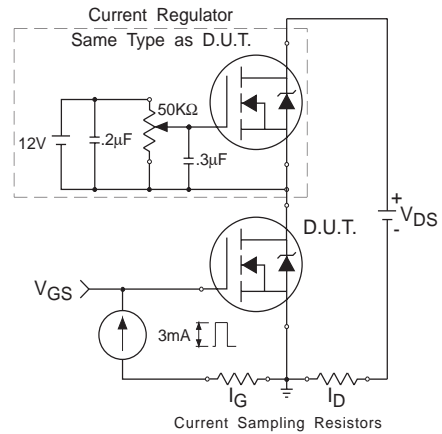
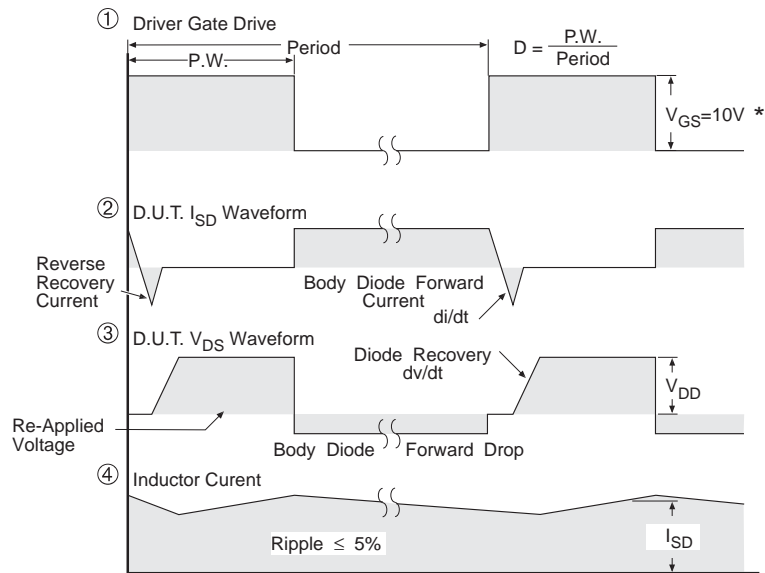


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

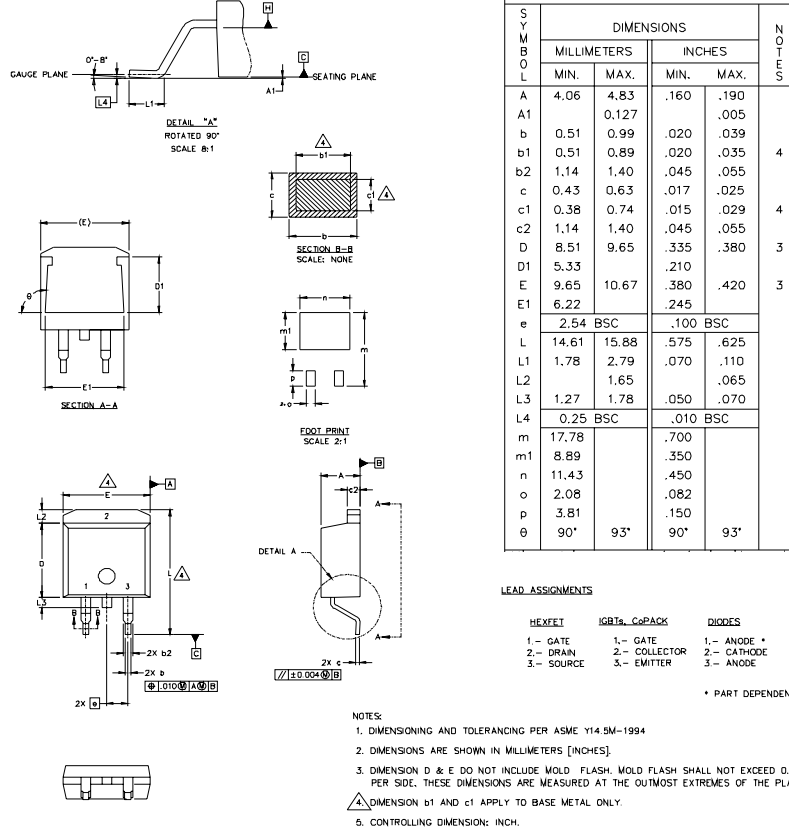
Fig 14. For N-Channel HEXFETS

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D²Pak Package Outline

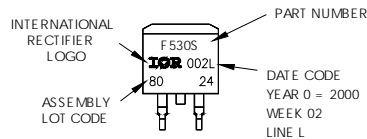
Dimensions are shown in millimeters (inches)



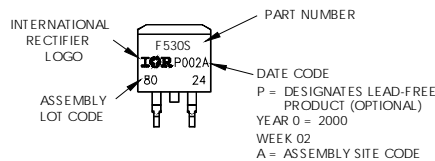
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"

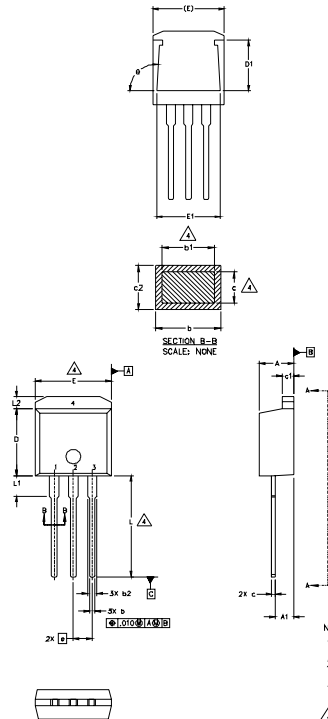


OR



TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

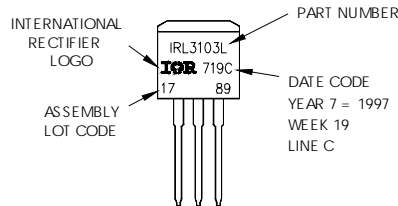
LEAD ASSIGNMENTS

HEXFET	IGBT
1.- GATE	1 - GATE
2.- DRAIN	2 - COLLECTOR
3.- SOURCE	3 - EMITTER
4.- DRAIN	

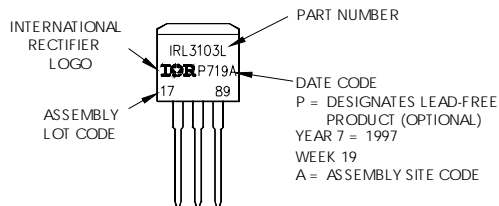
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
 Note: "P" in assembly line
 position indicates "Lead-Free"



OR

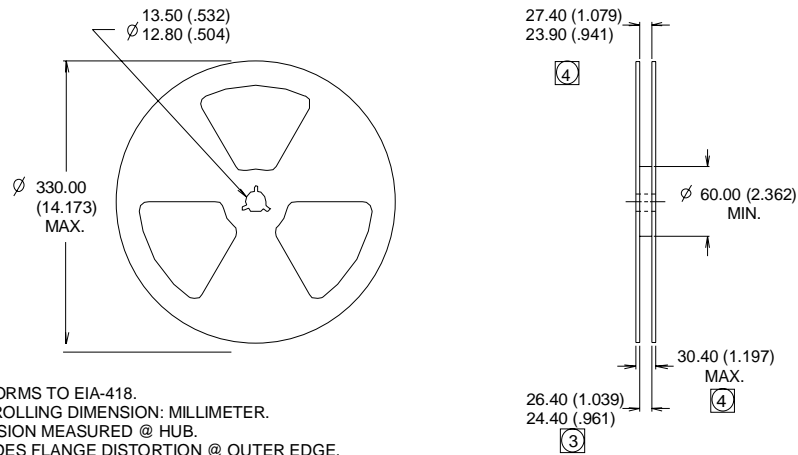
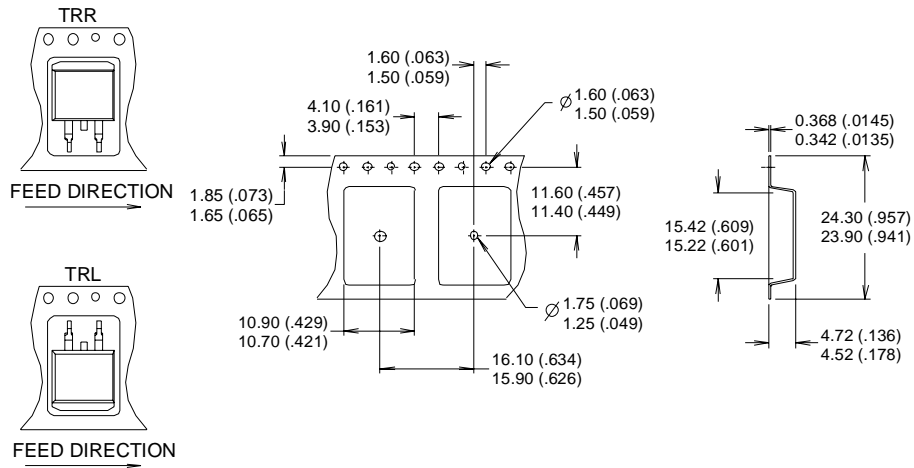


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D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.

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